# **BL** Galaxy Electrical

# Silicon Epitaxial Planar Transistor

#### 2SA812

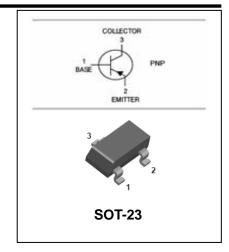
#### **FEATURES**

• Commplementary to 2SC1623.



High DC current gain:h<sub>FE</sub>=200typ.
(V<sub>CE</sub>=-6.0V,I<sub>C</sub>=-1.0mA)

● High Voltage: V<sub>CEO</sub>=-50V



#### **APPLICATIONS**

• Audio frequency, general purpose amplifier

#### ORDERING INFORMATION

Type No.	Marking	Package Code	
2SA812	M4/M5/M6/M7	SOT-23	

#### MAXIMUM RATING @ Ta=25℃ unless otherwise specified

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	-60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-50	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
Ic	Collector Current -Continuous	-100	mA
P <sub>C</sub>	Collector Dissipation	200	mW
$T_{j},T_{stg}$	Junction and Storage Temperature	-55~150	$^{\circ}$

Document number: BL/SSSTC010

Rev.A



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## ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-100μΑ,I <sub>E</sub> =0	-60			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-1mA,I <sub>B</sub> =0	-50			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-100μA,I <sub>C</sub> =0	-5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-60V,I <sub>E</sub> =0			-0.1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-5V,I <sub>C</sub> =0			-0.1	μΑ
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-6V,I <sub>C</sub> =-1mA	90	200	600	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-100mA, I <sub>B</sub> =-10mA			-0.3	V
Base-emitter voltage	$V_{BE}$	I <sub>C</sub> =-1mA, V <sub>CE</sub> =-6V	-0.58		-0.68	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-6V, I <sub>C</sub> =-10mA		180		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V,I <sub>E</sub> =0,f=1MHz		4.5		pF

#### CLASSIFICATION OF h<sub>FE(1)</sub>

Range	M4	M5	M6	M7
Marking	90-180	135-270	200-400	300-600

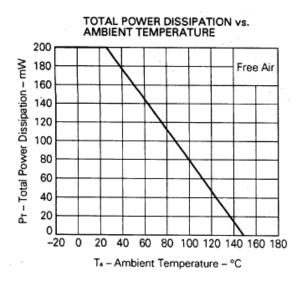
Document number: BL/SSSTC010

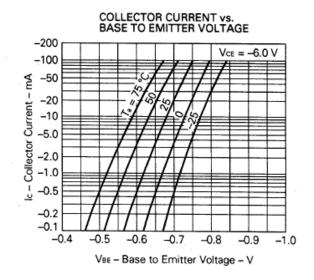
Rev.A

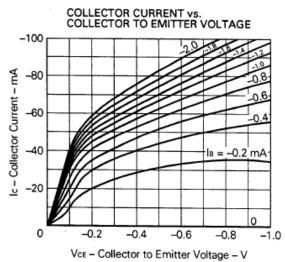
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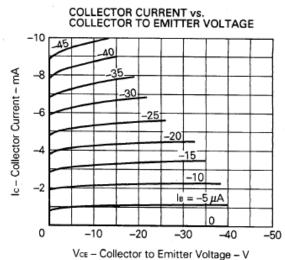
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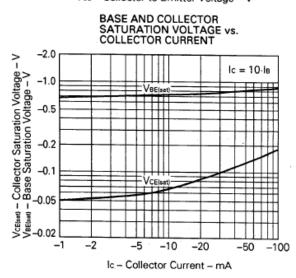
#### TYPICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

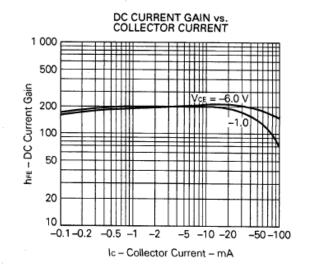












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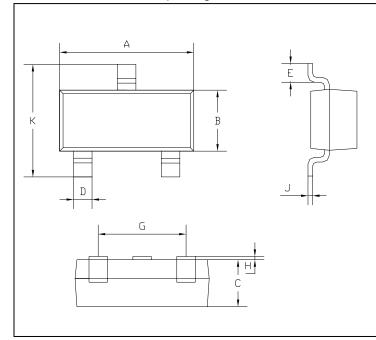
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#### PACKAGE OUTLINE

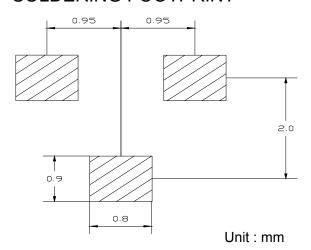
Plastic surface mounted package

SOT-23



SOT-23			
Dim	Min	Max	
Α	2.85	2.95	
В	1.25 1.35		
С	1.0Typical		
D	0.37	0.43	
E	0.35	0.48	
G	1.85	1.95	
Н	0.02 0.1		
J	0.1Typical		
K	2.35 2.45		
All Dimensions in mm			

#### **SOLDERING FOOTPRINT**



#### PACKAGE INFORMATION

Device	Package	Shipping
2SA812	SOT-23	3000/Tape&Reel

# www.s-manuals.com